

isc Silicon NPN Power Transistor

2SC898

DESCRIPTION

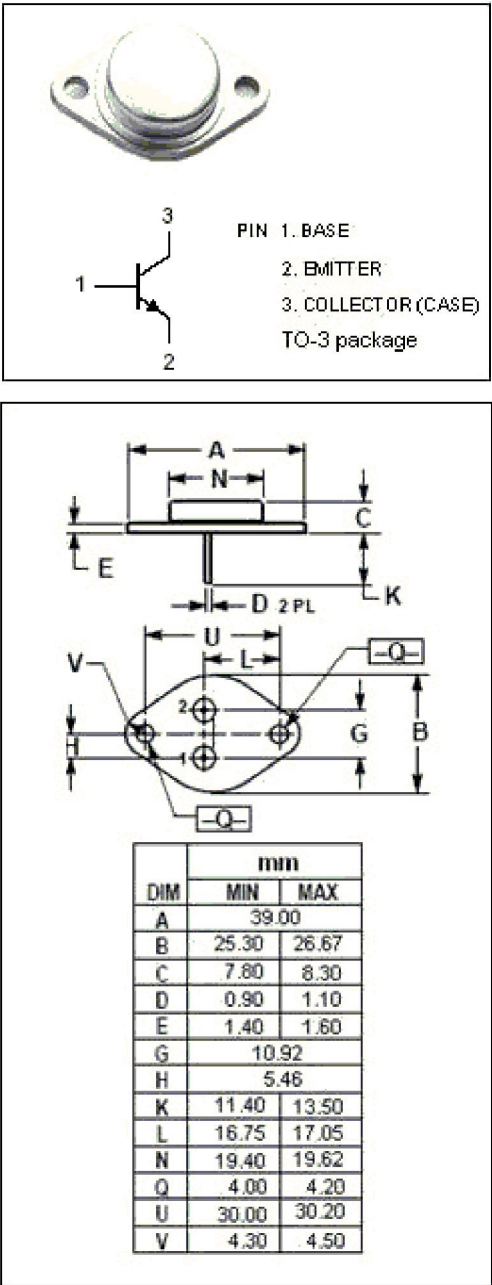
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 150V$ (Min)
- Low Collector Saturation Voltage-
: $V_{CE(sat)} = 1.5V$ (Max.)@ $I_C = 6A$

APPLICATIONS

- Designed for amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	MAX	UNIT
V_{CBO}	Collector-Base Voltage	150	V
V_{CEO}	Collector-Emitter Voltage	150	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	7	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}C$	80	W
T_j	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



isc Silicon NPN Power Transistor**2SC898****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 50mA; I _B = 0	150			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 6A; I _B = 1A			1.5	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 6A; I _B = 1A			1.8	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 150V; I _E = 0			1.0	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			1.0	mA
h _{FE}	DC Current Gain	I _C = 1A; V _{CE} = 5V	50			